

**TOSHIBA**

**TLP3020(S),TLP3021(S),TLP3022(S),TLP3023(S)**

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

# TLP3020(S), TLP3021(S), TLP3022(S), TLP3023(S)

OFFICE MACHINE

HOUSEHOLD USE EQUIPMENT

TRIAC DRIVER

SOLID STATE RELAY

Unit in mm

The TOSHIBA TLP3020 (S), TLP3021 (S), TLP3022 (S) and TLP3023 (S) consist of a photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

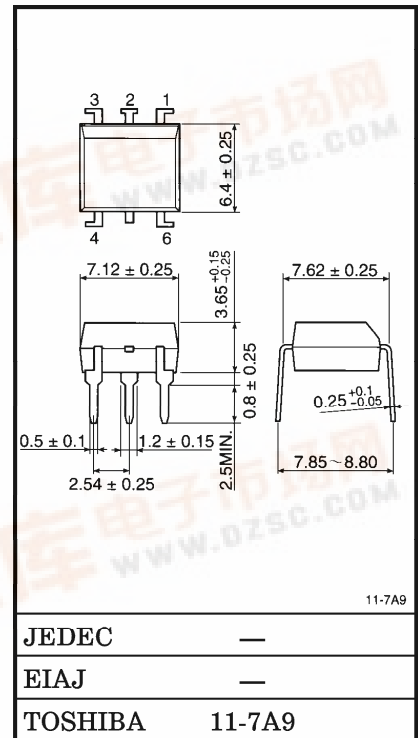
All parameters are tested to the specification of TLP3020, TLP3021, TLP3022, TLP3023.

- Peak Off-State Voltage : 400 V (Min.)
- Trigger LED Current : 30 mA (Max.) (TLP3020)  
15 mA (Max.) (TLP3021)  
10 mA (Max.) (TLP3022)  
5 mA (Max.) (TLP3023)
- On-State Current : 100 mA (Max.)
- UL Recognized : UL1577, File No. E67349
- Isolation Voltage : 5000 V<sub>rms</sub> (Min.)
- SEMKO Approved : SS EN60065  
SS EN60950  
SS EN60335
- Option (D4) Type  
VDE Approved : DIN VDE0884 / 06.92  
Certificate No. 68329

Maximum Operating Insulation Voltage : 890 V<sub>PK</sub>

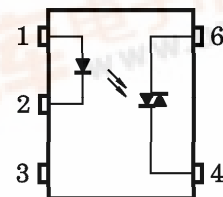
Highest Permissible Over Voltage : 8000 V<sub>PK</sub>

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"



Weight : 0.39 g

PIN CONFIGURATION (Top view)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : TERMINAL 1
- 6 : TERMINAL 2

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	7.62 mm pitch standard type	10.16 mm pitch (LF2) type
Creepage Distance	7.0 mm (Min.)	8.0 mm (Min.)
Clearance	7.0 mm (Min.)	8.0 mm (Min.)
Insulation Thickness	0.5 mm (Min.)	0.5 mm (Min.)